

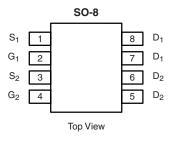
Dual N-Channel 20-V (D-S) MOSFET

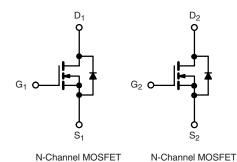
PRODUCT SUMMARY			
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	
20	0.019 at V _{GS} = 4.5 V	7.1	
	0.026 at V_{GS} = 2.5 V	6.0	

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC







ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted Symbol Limit Unit Parameter **Drain-Source Voltage** V_{DS} 20 ٧ Gate-Source Voltage V_{GS} ± 12 T_A = 25 °C 7.1 Continuous Drain Current (T_J = 150 °C)^a I_D T_A = 70 °C 5.7 А Pulsed Drain Current (10 µs Pulse Width) 40 I_{DM} 1.7 I_S Continuous Source Current (Diode Conduction)^a T_A = 25 °C 2 P_D w Maximum Power Dissipation^a T_A = 70 °C 1.3 Operating Junction and Storage Temperature Range T_J, T_{stg} - 55 to 150 °C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Maximum Junction-to-Ambient ^a	R _{thJA}	62.5	°C/W		

Notes:

a. Surface Mounted on FR4 board, t \leq 10 s.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.6		1.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
7	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	$_{3} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$		5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	20			А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 7.1 \text{ A}$	0.019				
		$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 6.0 \text{ A}$		0.026		Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 7.1 \text{ A}$		27		S	
Diode Forward Voltage ^a	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V			1.2	V	
Dynamic ^b			•				
Total Gate Charge	Qg			9.5		nC	
Gate-Source Charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 7.1 A		1.5			
Gate-Drain Charge	Q _{gd}			2.5			
Gate Resistance	R _g	f = 1 MHz		1.6	2.7	Ω	
Turn-On Delay Time	t _{d(on)}			10			
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		15		ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_g = 10 Ω		38			
Fall Time	t _f			25			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dl/dt = 100 A/μs		26			

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

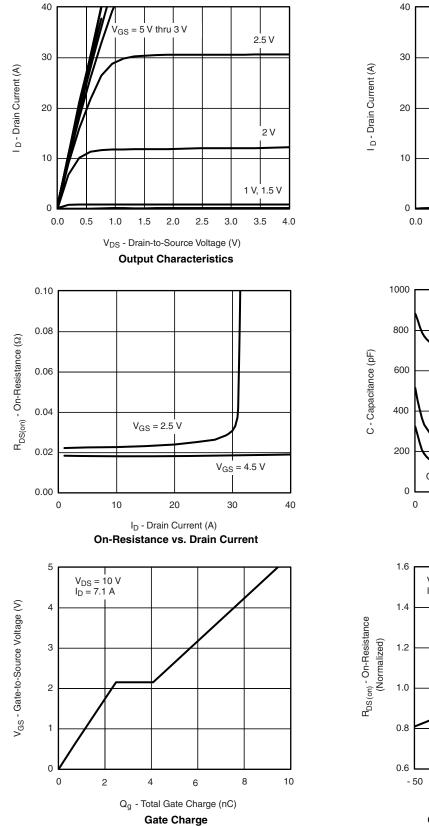
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

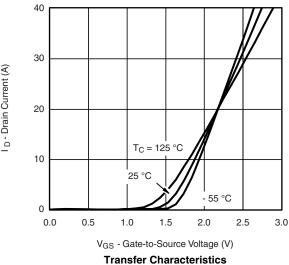
Bsemi

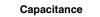
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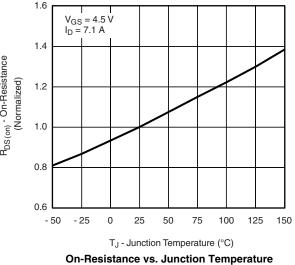




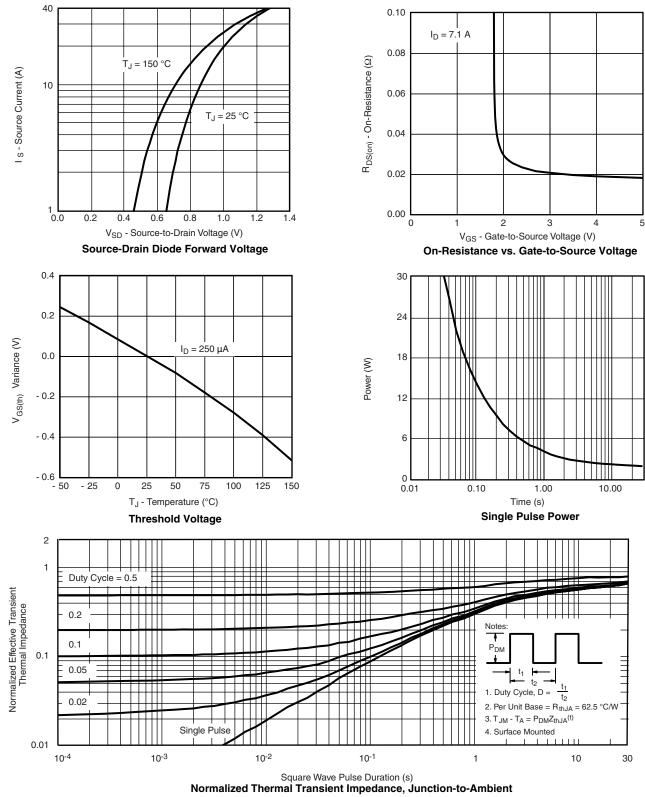
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



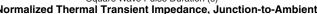








TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

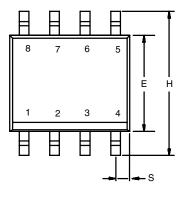


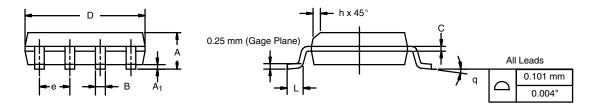




SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012

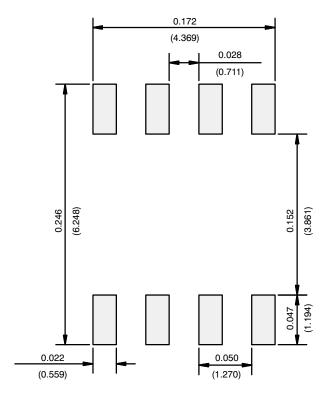




	MILLIM	IETERS	INCHES		
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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